



THE DATASHEET OF MIC5013YM



General Description

The MIC5013 is an 8-pin MOSFET driver with over-current shutdown and a fault flag. It is designed to drive the gate of an N-channel power MOSFET above the supply rail high-side power switch applications. The MIC5013 is compatible with standard or current-sensing power MOSFETs in both high- and low-side driver topologies.

The MIC5013 charges a 1nF load in 60µs typical and protects the MOSFET from over-current conditions. The current sense trip point is fully programmable and a dynamic threshold allows high in-rush current loads to be started. A fault pin indicates when the MIC5013 has turned off the FET due to excessive current.

Other members of the Micrel driver family include the MIC5011 minimum parts count driver and MIC5012 dual driver.

Features

- 7V to 32V operation
- Less than 1µA standby current in the “OFF” state
- Available in small outline SOIC packages
- Internal charge pump to drive the gate of an N-channel power FET above supply
- Internal zener clamp for gate protection
- 60µs typical turn-on time to 50% gate overdrive
- Programmable over-current sensing
- Dynamic current threshold for high in-rush loads
- Fault output pin indicates current faults
- Implements high- or low-side switches

Applications

- Lamp drivers
- Relay and solenoid drivers
- Heater switching
- Power bus switching
- Motion control

Typical Application

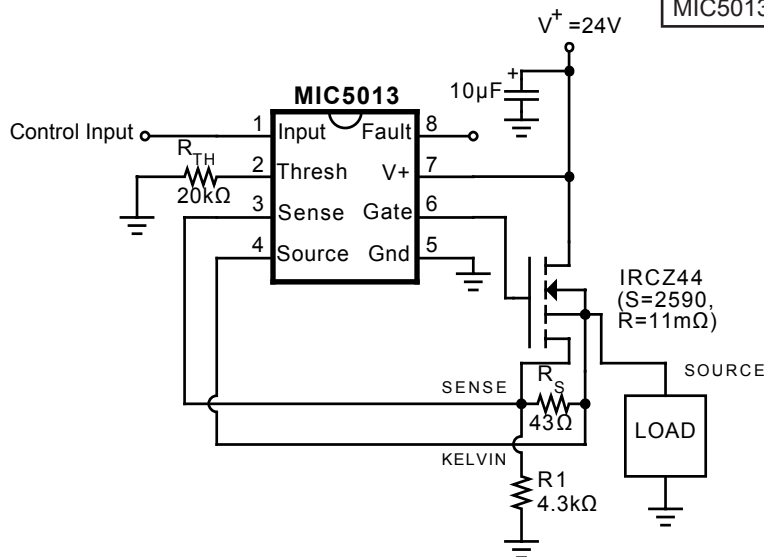


Figure 1. High-Side Driver with Current-Sensing MOSFET

Ordering Information

Part Number		Temperature Range	Package
Standard	Pb-Free		
MIC5013BN	MIC5013YN	-40°C to +85°C	8-pin Plastic DIP
MIC5013BM	MIC5013YM	-40°C to +85°C	8-pin SOIC

$$R_S = \frac{SR(V_{TRIP} + 100mV)}{I_L - (V_{TRIP} + 100mV)}$$

$$R1 = \frac{V^+SR R_S}{100mV(SR + R_S)}$$

$$R_{TH} = \frac{2200}{V_{TRIP}} - 1000$$

For this example:

$$I_L = 30A \text{ (trip current)}$$

$$V_{TRIP} = 100mV$$

Note: The MIC5013 is ESD sensitive.

Protected under one or more of the following Micrel patents:
patent #4,951,101; patent #4,914,546

Absolute Maximum Ratings (Note 1, 2)

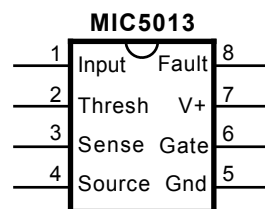
Input Voltage, Pin 1	-10 to V ⁺
Threshold Voltage, Pin 2	-0.5 to +5V
Sense Voltage, Pin 3	-10V to V ⁺
Source Voltage, Pin 4	-10V to V ⁺
Current into Pin 4	50mA
Gate Voltage, Pin 6	-1V to 50V
Supply Voltage (V ⁺), Pin 7	-0.5V to 36V
Fault Output Current, Pin 8	-1mA to +1mA
Junction Temperature	150°C

Operating Ratings (Notes 1, 2)

Power Dissipation	1.25W
θ_{JA} (Plastic DIP)	100°C/W
θ_{JA} (SOIC)	170°C/W
Ambient Temperature: B version	-40°C to +85°C
Storage Temperature	-65°C to +150°C
Lead Temperature (Soldering, 10 seconds)	260°C
Supply Voltage (V ⁺), Pin 7	7V to 32V high side 7V to 15V low side

Pin Description (Refer to Figures 1 and 2)

Pin Number	Pin Name	Pin Function
1	Input	Resets current sense latch and turns on power MOSFET when taken above threshold (3.5V typical). Pin 1 requires <1 μ A to switch.
2	Threshold	Sets current sense trip voltage according to: $V_{TRIP} = \frac{2200}{R_{TH} + 1000}$ where R _{TH} to ground is 3.3k to 20k Ω . Adding capacitor C _{TH} increases the trip voltage at turn-on to 2V. Use C _{TH} = 10 μ F for a 10ms turn-on time constant.
3	Sense	The sense pin causes the current sense to trip when V _{SENSE} is V _{TRIP} above V _{SOURCE} . Pin 3 is used in conjunction with a current shunt in the source of a 3 lead FET or a resistor R _S in the sense lead of a current sensing FET.
4	Source	Reference for the current sense voltage on pin 3 and return for the gate clamp zener. Connect to the load side of current shunt or kelvin lead of current sensing FET. Pins 3 and 4 can safely swing to -10V when turning off inductive loads.
5	Ground	
6	Gate	Drives and clamps the gate of the power FET. Pin 6 will be clamped to approximately -0.7V by an internal diode when turning off inductive loads.
7	V ⁺	Supply pin; must be decoupled to isolate from large transients caused by the power FET drain. 10 μ F is recommended close to pins 7 and 5.
8	Fault	Outputs status of protection circuit when pin 1 is high. Fault low indicates normal operation; fault high indicates current sense tripped.

Pin Configuration

Electrical Characteristics (Note 3, 5)

Test circuit. $T_A = -55^\circ\text{C}$ to $+125^\circ\text{C}$, $V^+ = 15\text{V}$, all switches open, unless otherwise specified.

Parameter	Conditions		Min	Typical	Max	Units	
Supply Current, I_7	$V^+ = 32\text{V}$	$V_{\text{IN}} = 0\text{V}$, S4 closed		0.1	10	μA	
		$V_{\text{IN}} = V_S = 32\text{V}$		8	20	mA	
Logic Input Voltage, V_{IN}	$V^+ = 4.75\text{V}$	Adjust V_{IN} for V_{GATE} low			2	V	
		Adjust V_{IN} for V_{GATE} high	4.5			V	
Logic Input Current, I_1	$V^+ = 15\text{V}$	Adjust V_{IN} for V_{GATE} high	5.0			V	
		$V_{\text{IN}} = 0\text{V}$	-1			μA	
Input Capacitance	Pin 1	$V_{\text{IN}} = 32\text{V}$			1	μA	
				5		pF	
Gate Drive, V_{GATE}	S1, S2 closed, $V_S = V^+$, $V_{\text{IN}} = 5\text{V}$	$V^+ = 7\text{V}$, $I_6 = 0$	13	15		V	
		$V^+ = 15\text{V}$, $I_6 = 100\ \mu\text{A}$	24	27		V	
Zener Clamp, $V_{\text{GATE}} - V_{\text{SOURCE}}$	S2 closed, $V_{\text{IN}} = 5\text{V}$	$V^+ = 15\text{V}$, $V_S = 15\text{V}$	11	12.5	15	V	
		$V^+ = 32\text{V}$, $V_S = 32\text{V}$	11	13	16	V	
Gate Turn-on Time, t_{ON} μs (Note 4)	V_{IN} switched from 0 to 5V; measure time for V_{GATE} to reach 20V				60	200	
Gate Turn-off Time, t_{OFF}	V_{IN} switched from 5 to 0V; measure time for V_{GATE} to reach 1V			4	10	μs	
Threshold Bias Voltage, V_2	$I_2 = 200\ \mu\text{A}$		1.7	2	2.2	V	
Current Sense Trip Voltage, $V_{\text{SENSE}} - V_{\text{SOURCE}}$	S2 closed, $V_{\text{IN}} = 5\text{V}$, Increase I_3	$V^+ = 7\text{V}$, $I_2 = 100\ \mu\text{A}$	S4 closed	75	105	135	mV
			$V_S = 4.9\text{V}$, S4 open	70	100	130	mV
		$V^+ = 15\text{V}$, $I_2 = 200\ \mu\text{A}$	S4 closed	150	210	270	mV
			$V_S = 11.8\text{V}$, S4 open	140	200	260	mV
		$V^+ = 32\text{V}$, $I_2 = 500\ \mu\text{A}$	$V_S = 0\text{V}$, S4 open	360	520	680	mV
$V_S = 25.5\text{V}$, S4 open	350	500	650	mV			
Peak Current Trip Voltage, $V_{\text{SENSE}} - V_{\text{SOURCE}}$	S3, S4 closed, $V^+ = 15\text{V}$, $V_{\text{IN}} = 5\text{V}$		1.6	2.1		V	
Fault Output Voltage, V_8	$V_{\text{IN}} = 0\text{V}$, $I_8 = -100\ \mu\text{A}$			0.4	1	V	
	$V_{\text{IN}} = 5\text{V}$, $I_8 = 100\ \mu\text{A}$, current sense tripped		14	14.6		V	

Note 1. Absolute Maximum Ratings indicate limits beyond which damage to the device may occur. Electrical specifications do not apply when operating the device beyond its specified **Operating Ratings**.

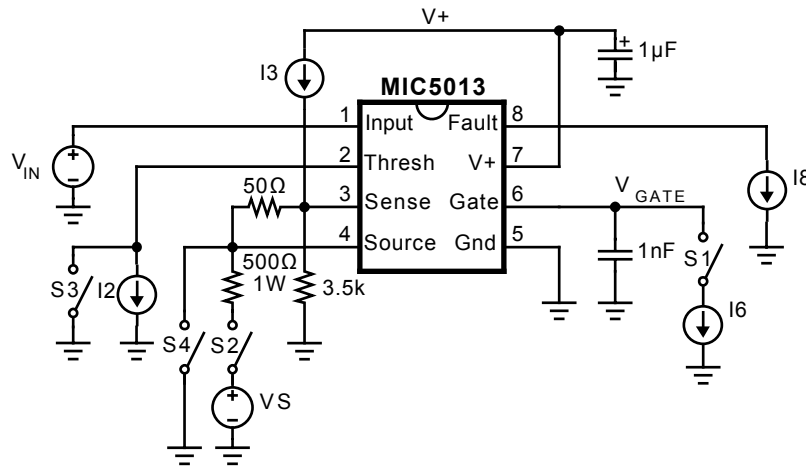
Note 2. The MIC5010 is ESD sensitive.

Note 3. Minimum and maximum **Electrical Characteristics** are 100% tested at $T_A = 25^\circ\text{C}$ and $T_A = 85^\circ\text{C}$, and 100% guaranteed over the entire range. Typicals are characterized at 25°C and represent the most likely parametric norm.

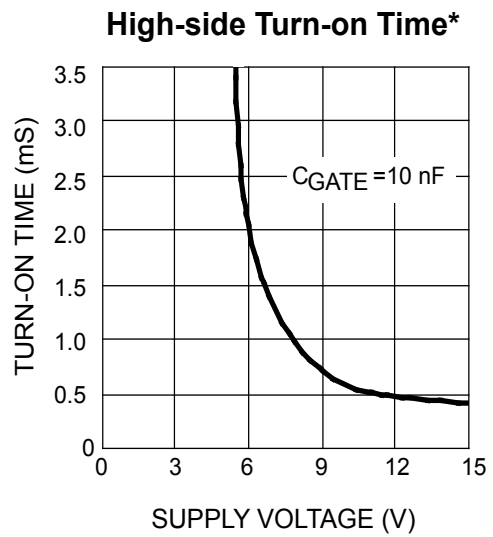
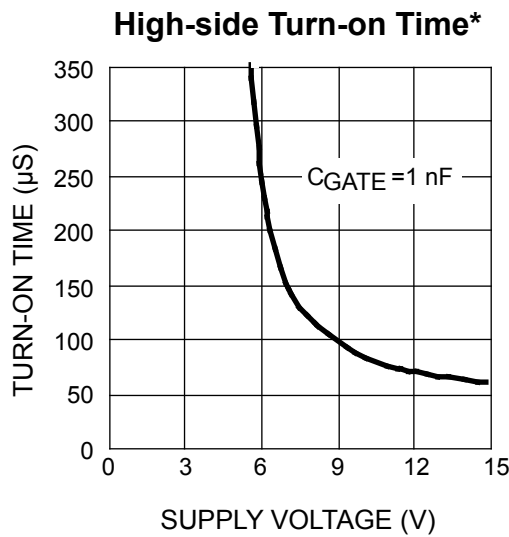
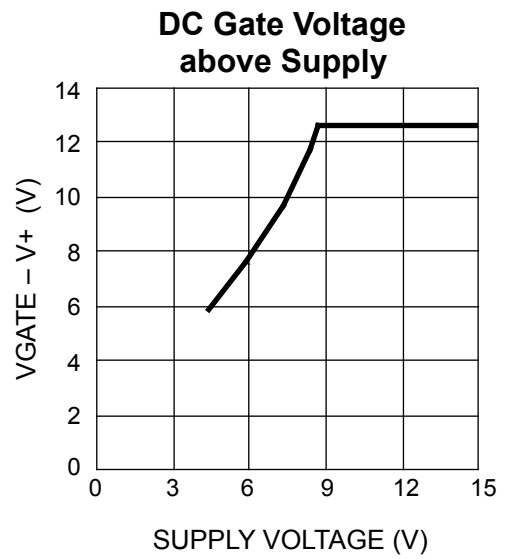
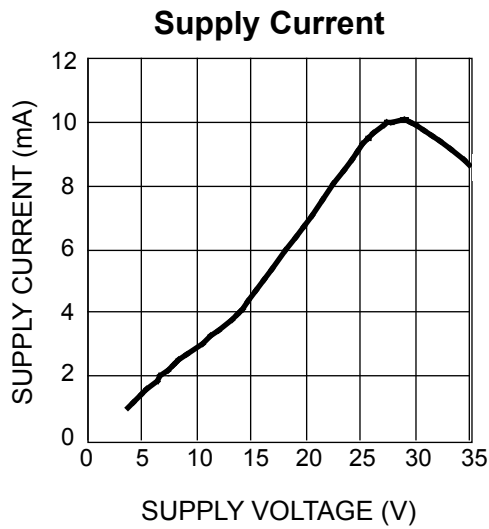
Note 4. Test conditions reflect worst case high-side driver performance. Low-side and bootstrapped topologies are significantly faster—see **Applications Information**.

Note 5. Specification for packaged product only.

Test Circuit



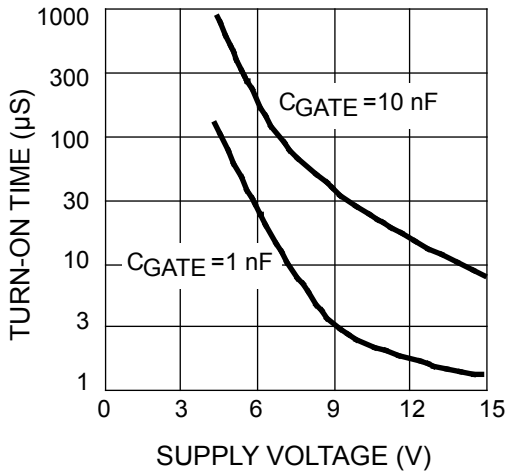
Typical Characteristics



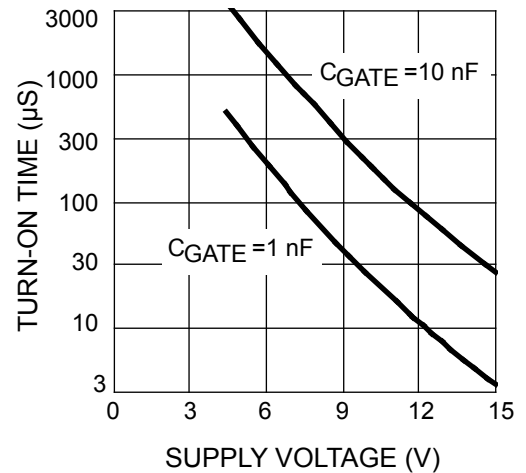
* Time for gate to reach V+ + 5V in test circuit with VS = V+ - 5V (prevents gate clamp from interfering with measurement).

Typical Characteristics (Continued)

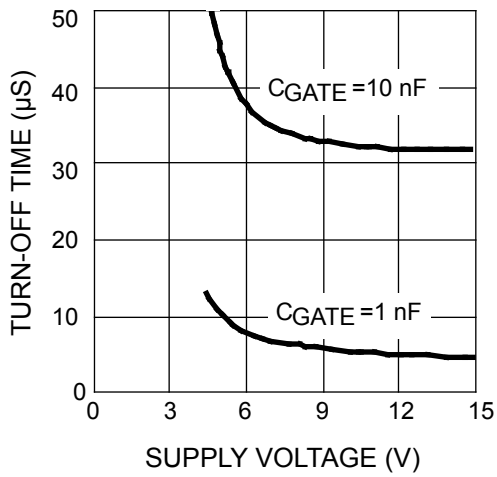
Low-side Turn-on Time for Gate = 5V



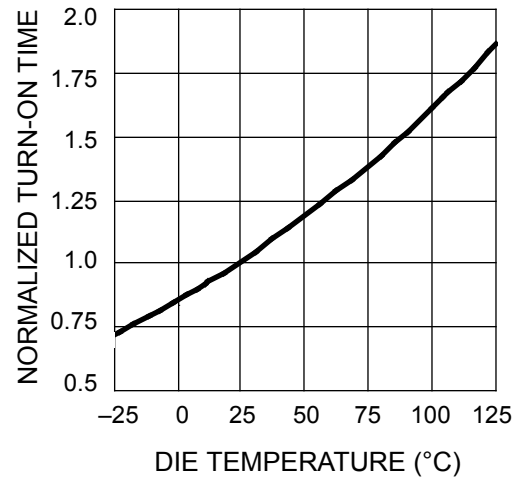
Low-side Turn-on Time for Gate = 10V



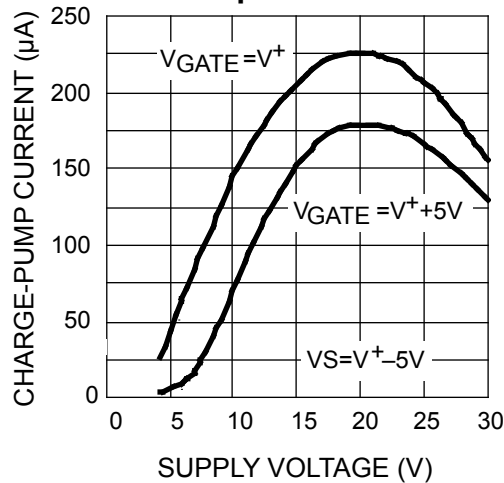
Turn-off Time



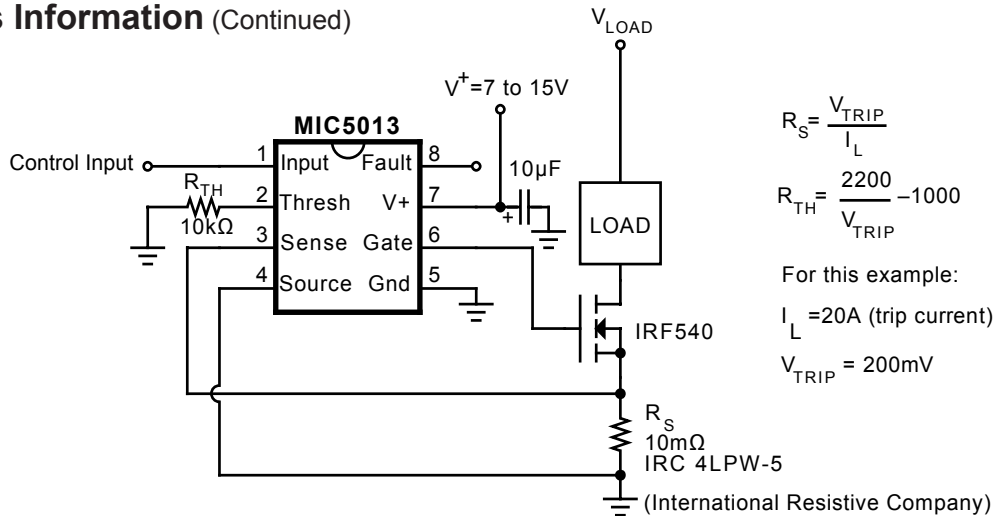
Turn-on Time



Charge Pump Output Current



Applications Information (Continued)



$$R_S = \frac{V_{TRIP}}{I_L}$$

$$R_{TH} = \frac{2200}{V_{TRIP}} - 1000$$

For this example:

$$I_L = 20A \text{ (trip current)}$$

$$V_{TRIP} = 200mV$$

(International Resistive Company)

Figure 2. Low-Side Driver with Current Shunt

Circuit Topologies

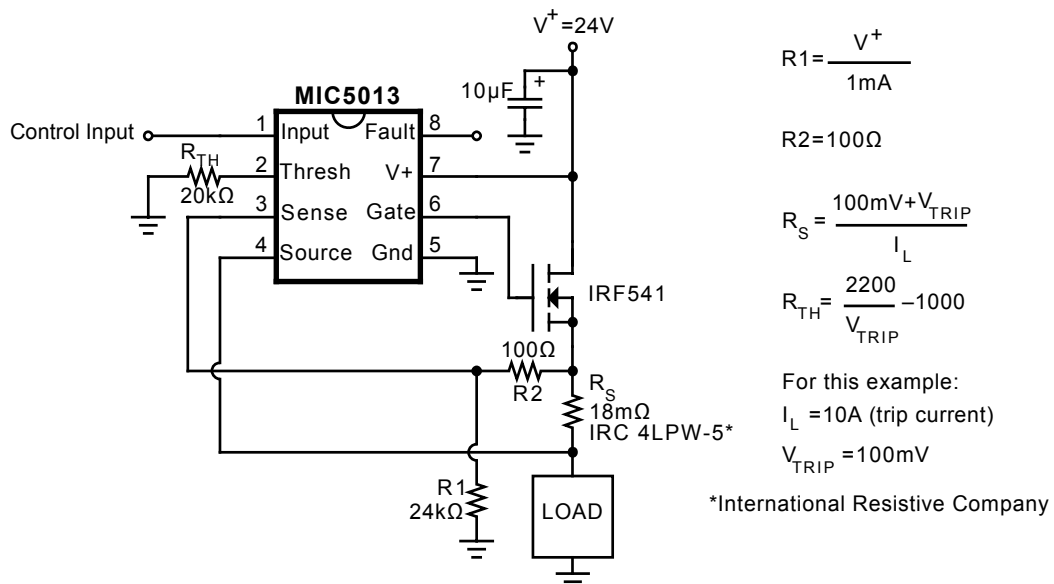
The MIC5013 is suited for use in high- or low-side driver applications with over-current protection for both current-sensing and standard MOSFETs. In addition, the MIC5013 works well in applications where, for faster switching times, the supply is bootstrapped from the MOSFET source output. Low voltage, high-side drivers (such as shown in the Test Circuit) are the slowest; their speed is reflected in the gate turn-on time specifications. The fastest drivers are the low-side and bootstrapped high-side types. Load current switching times are often much faster than the time to full gate enhancement, depending on the circuit type, the MOSFET, and the load. Turn-off times are essentially the same for all circuits (less than 10μs to $V_{GS} = 1V$). The choice of one topology over another is based on a combination of considerations including speed, voltage, and desired system characteristics. Each topology is described in this section. Note that I_L , as used in the design equations, is the load current that just trips the over-current comparator.

Low-Side Driver with Current Shunt (Figure 2). The over-current comparator monitors R_S and trips if $I_L \times R_S$ exceeds V_{TRIP} . R is selected to produce the desired trip voltage.

As a guideline, keep V_{TRIP} within the limits of 100mV and 500mV ($R_{TH} = 3.3k\Omega$ to $20k\Omega$). Thresholds at the high end offer the best noise immunity, but also compromise switch drop (especially in low voltage applications) and power dissipation.

The trip current is set higher than the maximum expected load current—typically twice that value. Trip point accuracy is a function of resistor tolerances, comparator offset (only a few millivolts), and threshold bias voltage (V_2). The values shown in Figure 2 are designed for a trip current of 20 amperes. It is important to ground pin 4 at the current shunt R_S , to eliminate the effects of ground resistance.

A key advantage of the low-side topology is that the load supply is limited only by the MOSFET BVDSS rating. Clamping may be required to protect the MOSFET drain terminal from



$$R_1 = \frac{V^+}{1mA}$$

$$R_2 = 100\Omega$$

$$R_S = \frac{100mV + V_{TRIP}}{I_L}$$

$$R_{TH} = \frac{2200}{V_{TRIP}} - 1000$$

For this example:

$$I_L = 10A \text{ (trip current)}$$

$$V_{TRIP} = 100mV$$

*International Resistive Company

Figure 3. High-Side Driver with Current Shunt

Applications Information (Continued)

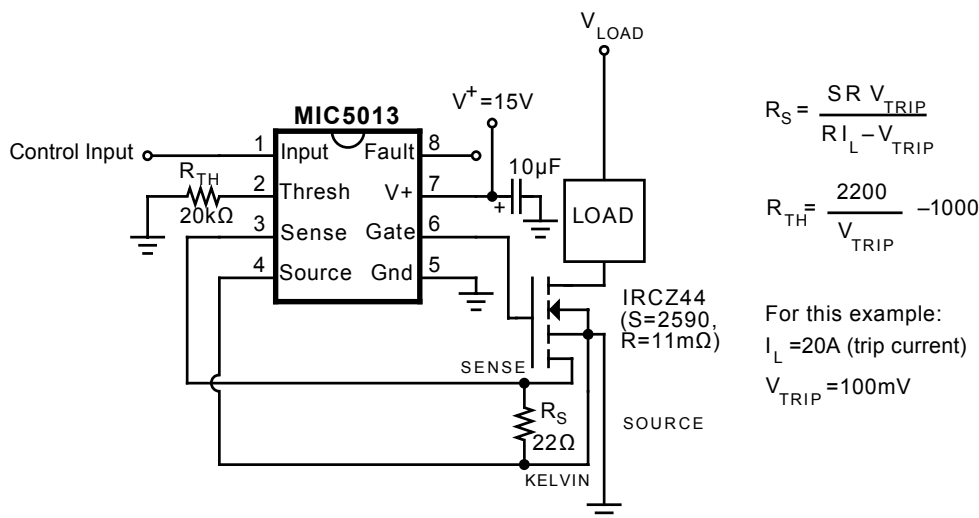


Figure 4. Low-Side Driver with Current-Sensing MOSFET

inductive switching transients. The MIC5013 supply should be limited to 15V in low-side topologies; otherwise, a large current will be forced through the gate clamp zener.

Low-side drivers constructed with the MIC501X family are also fast; the MOSFET gate is driven to near supply immediately when commanded ON. Typical circuits achieve 10V enhancement in 10μs or less on a 12 to 15V supply.

High-Side Driver with Current Shunt (Figure 3). The comparator input pins (source and sense) float with the current sensing resistor (R_S) on top of the load. R1 and R2 add a small, additional potential to V_{TRIP} to prevent false-triggering of the over-current shutdown circuit with open or inductive loads. R1 is sized for a current flow of 1mA, while R2 contributes a drop of 100mV. The shunt voltage should be 200 to 500mV at the trip point. The example of Figure 3 gives a 10A trip current when the output is near supply. The trip point is somewhat reduced when the output is at ground as the voltage drop across R1 (and therefore R2) is zero.

High-side drivers implemented with MIC5013 drivers are self-protected against inductive switching transients. During turn-off an inductive load will force the MOSFET source 5V or more below ground, while the driver holds the gate at ground potential. The MOSFET is forced into conduction, and it dissipates the energy stored in the load inductance. The MIC5013 source and sense pins (3 and 4) are designed to withstand this negative excursion without damage. External clamp diodes are unnecessary.

Current Shunts (R_S). Low-valued resistors are necessary for use at R_S . Values for R_S range from 5 to 50mΩ, at 2 to 10W. Worthy of special mention are Kelvin-sensed, "four-terminal" units supplied by a number of manufacturers†

(see next page). Kelvin-sensed resistors eliminate errors caused by lead and terminal resistances, and simplify product assembly. 10% tolerance is normally adequate, and with shunt potentials of 200mV thermocouple effects are insignificant. Temperature coefficient is important; a linear, 500 ppm/°C change will contribute as much as 10% shift in the over-current trip point. Most power resistors designed for current shunt service drift less than 100 ppm/°C.

Low-Side Driver with Current Sensing MOSFET (Figure 4). Several manufacturers now supply power MOSFETs in which a small sampling of the total load current is diverted to a "sense" pin. One additional pin, called "Kelvin source," is included to eliminate the effects of resistance in the source bond wires. Current-sensing MOSFETs are specified with a sensing ratio "S" which describes the relationship between the on-resistance of the sense connection and the body resistance "R" of the main source pin. Current sensing MOSFETs eliminate the current shunt required by standard MOSFETs.

The design equations for a low-side driver using a current sensing MOSFET are shown in Figure 4. "S" is specified on the MOSFET's datasheet, and "R" must be measured or estimated. V_{TRIP} must be less than $R \times I_L$, or else R_S will become negative. Substituting a MOSFET with higher on-resistance, or reducing V_{TRIP} fixes this problem. $V_{TRIP} = 100$ to 200mV is suggested. Although the load supply is limited only by MOSFET ratings, the MIC5013 supply should be limited to 15V to prevent damage to the gate clamp zener. Output clamping is necessary for inductive loads.

"R" is the body resistance of the MOSFET, excluding bond resistances. $R_{DS(ON)}$ as specified on MOSFET data sheets includes bond resistances. A Kelvin-connected ohmmeter

† Suppliers of Kelvin-sensed power resistors:

Dale Electronics, Inc., 2064 12th Ave., Columbus, NE 68601. Tel: (402) 564-3131

International Resistive Co., P.O. Box 1860, Boone, NC 28607-1860. Tel: (704) 264-8861

Kelvin, 14724 Ventura Blvd., Ste. 1003, Sherman Oaks, CA 91403-3501. Tel: (818) 990-1192

RCD Components, Inc., 520 E. Industrial Pk. Dr., Manchester, NH 03103. Tel: (603) 669-0054

Ultronix, Inc., P.O. Box 1090, Grand Junction, CO 81502. Tel: (303) 242-0810

Applications Information (Continued)

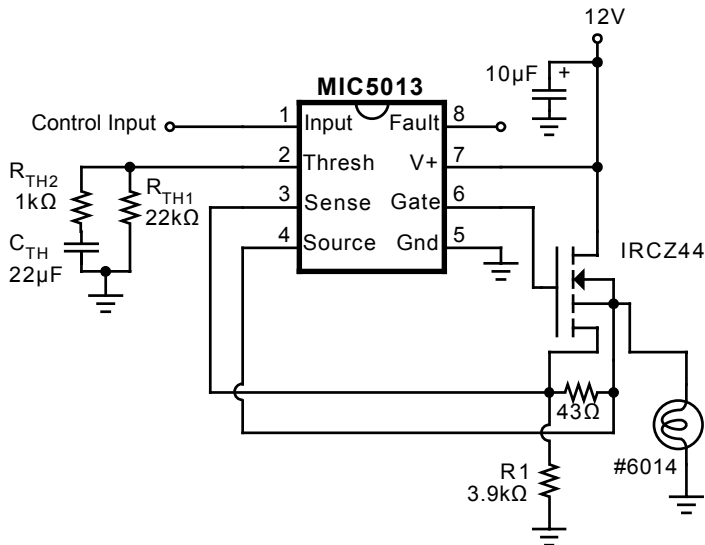


Figure 5. Time-Variable Trip Threshold

(using TAB and SOURCE for forcing, and SENSE and KELVIN for sensing) is the best method of evaluating “R.” Alternatively, “R” can be estimated for large MOSFETs ($R_{DS(ON)} \leq 100\text{m}\Omega$) by simply halving the stated $R_{DS(ON)}$, or by subtracting 20 to 50mΩ from the stated $R_{DS(ON)}$ for smaller MOSFETs.

High-Side Driver with Current Sensing MOSFET (Figure 5). The design starts by determining the value of “S” and “R” for the MOSFET (use the guidelines described for the low-side version). Let $V_{TRIP} = 100\text{mV}$, and calculate R_S for a desired trip current. Next calculate R_{TH} and R1. The trip point is somewhat reduced when the output is at ground as the voltage drop across R1 is zero. No clamping is required for inductive loads, but may be added to reduce power dissipation in the MOSFET.

Typical Applications

Start-up into a Dead Short. If the MIC5013 attempts to turn on a MOSFET when the load is shorted, a very high current flows. The over-current shutdown will protect the MOSFET, but only after a time delay of 5 to 10μs. The MOSFET must be capable of handling the overload; consult the device’s SOA curve. If a short circuit causes the MOSFET to exceed its 10μs SOA, a small inductance in series with the source can help limit di/dt to control the peak current during the 5 to 10μs delay.

When testing short-circuit behavior, use a current probe rated for both the peak current and the high di/dt.

The over-current shutdown delay varies with comparator overdrive, owing to noise filtering in the comparator. A delay of up to 100μs can be observed at the threshold of shutdown. A 20% overdrive reduces the delay to near minimum.

Incandescent Lamps. The cold filament of an incandescent lamp exhibits less than one-tenth as much resistance as when the filament is hot. The initial turn-on current of a #6014 lamp is about 70A, tapering to 4.4A after a few hundred milliseconds. It is unwise to set the over-current

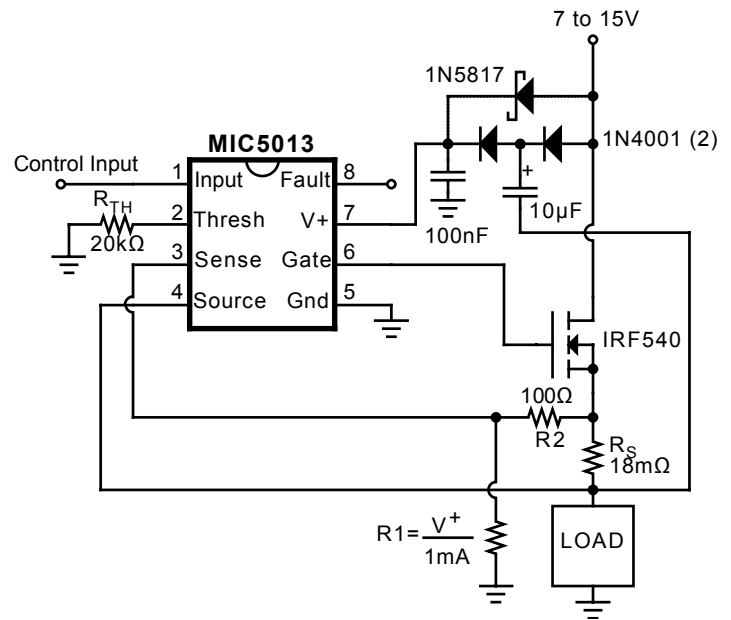


Figure 6. Bootstrapped High-Side Driver

trip point to 70A to accommodate such a load. A “resistive” short that draws less than 70A could destroy the MOSFET by allowing sustained, excessive dissipation. If the over-current trip point is set to less than 70A, the MIC5013 will not start a cold filament. The solution is to start the lamp with a high trip point, but reduce this to a reasonable value after the lamp is hot.

The MIC5013 over-current shutdown circuit is designed to handle this situation by varying the trip point with time (see Figure 5). R_{TH1} functions in the conventional manner, providing a current limit of approximately twice that required by the lamp. R_{TH2} acts to increase the current limit at turn-on to approximately 10 times the steady-state lamp current. The high initial trip point decays away according to a 20ms time constant contributed by C_{TH} . R_{TH2} could be eliminated with C_{TH} working against the internal 1kΩ resistor, but this results in a very high over-current threshold. As a rule of thumb design the over-current circuitry in the conventional manner, then add the R_{TH2}/C_{TH} network to allow for lamp start-up. Let $R_{TH2} = (R_{TH1} \div 10) - 1\text{k}\Omega$, and choose a capacitor that provides the desired time constant working against R_{TH2} and the internal 1kΩ resistor.

When the MIC5013 is turned off, the threshold pin (2) appears as an open circuit, and C_{TH} is discharged through R_{TH1} and R_{TH2} . This is much slower than the turn-on time constant, and it simulates the thermal response of the filament. If the lamp is pulse-width modulated, the current limit will be reduced by the residual charge left in C_{TH} .

Modifying Switching Times. Do not add external capacitors to the gate to slow down the switching time. Add a resistor (1kΩ to 51kΩ) in series with the gate of the MOSFET to achieve this result.

Bootstrapped High-Side Driver (Figure 6). The speed of a high-side driver can be increased to better than 10μs by bootstrapping the supply off of the MOSFET source. This topology can be used where the load is pulse-width modulated (100Hz to 20kHz), or where it is energized

Applications Information (Continued)

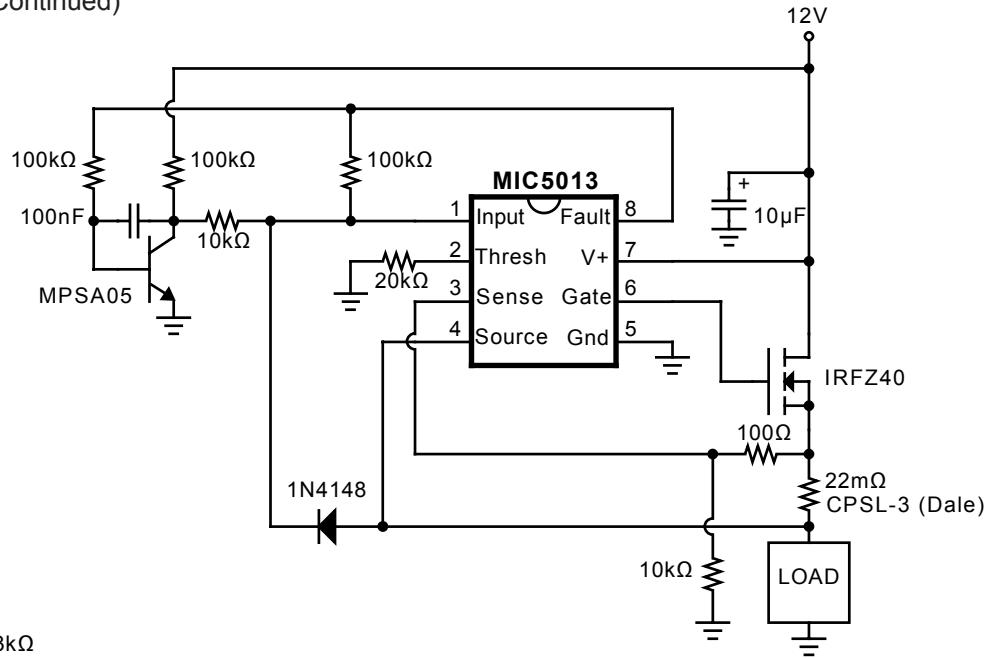


Figure 7. 10-Ampere Electronic Circuit Breaker

for only a short period of time ($\leq 25\text{ms}$). If the load is left energized for a long period of time ($> 25\text{ms}$), the bootstrap capacitor will discharge and the MIC5013 supply pin will fall to $V^+ = V_{DD} - 1.4$. Under this condition pins 3 and 4 will be held above V^+ and may false trigger the over-current circuit. A larger capacitor will lengthen the maximum “on” time; $1000\mu\text{F}$ will hold the circuit up for 2.5 seconds, but requires more charge time when the circuit is turned off. The optional Schottky barrier diode improves turn-on time on supplies of less than 10V.

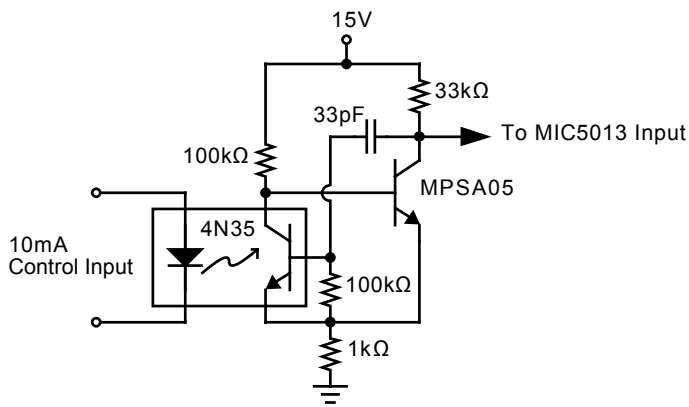


Figure 8. Improved Opto-Isolator Performance

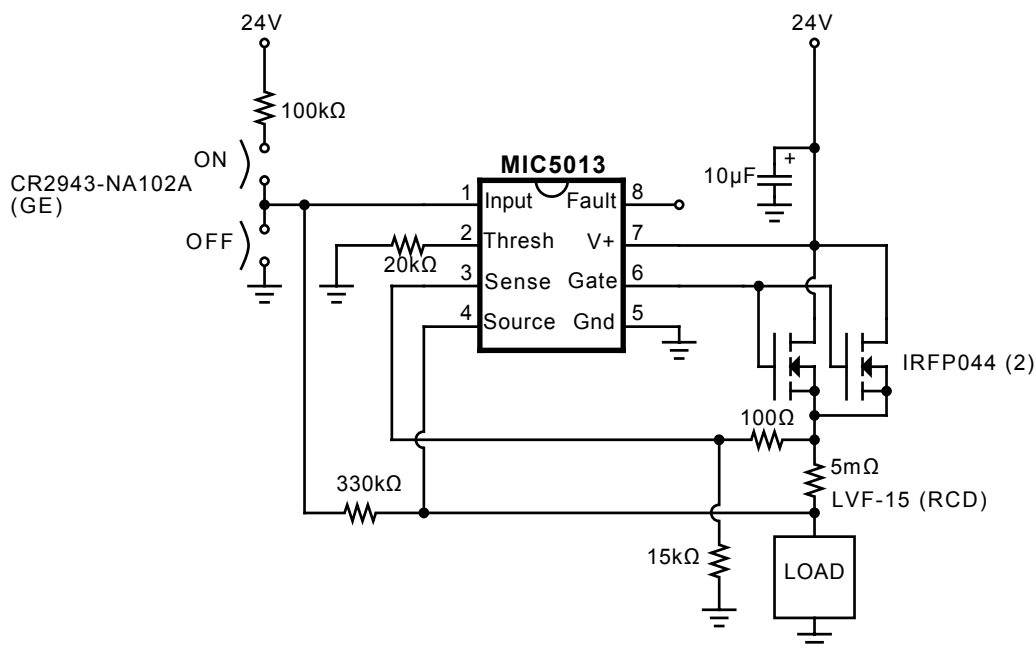


Figure 9. 50-Ampere Industrial Switch

Applications Information (Continued)

Since the supply current in the “OFF” state is only a small leakage, the 100nF bypass capacitor tends to remain charged for several seconds after the MIC5013 is turned off. In a PWM application the chip supply is actually much higher than the system supply, which improves switching time.

Electronic Circuit Breaker (Figure 7). The MIC5013 forms the basis of a high-performance, fast-acting circuit breaker. By adding feedback from FAULT to INPUT the breaker can be made to automatically reset. If an over-current condition occurs, the circuit breaker shuts off. The breaker tests the load every 18ms until the short is removed, at which time the circuit latches ON. No reset button is necessary.

Opto-Isolated Interface (Figure 8). Although the MIC5013 has no special input slew rate requirement, the lethargic transitions provided by an opto-isolator may cause oscillations on the rise and fall of the output. The circuit shown accelerates the input transitions from a 4N35 opto-isolator by adding hysteresis. Opto-isolators are used where the control circuitry cannot share a common ground with the MIC5013 and high-current power supply, or where the control circuitry is located remotely. This implementation is intrinsically safe; if the control line is severed the MIC5013 will turn OFF.

Fault-Protected Industrial Switch (Figure 9). The most common manual control for industrial loads is a push button on/off switch. The “on” button is physically arranged in a recess so that in a panic situation the “off” button, which extends out from the control box, is more easily pressed. This circuit is compatible with control boxes such as the CR2943 series (GE). The circuit is configured so that if both switches close simultaneously, the “off” button has precedence. If there is a fault condition the circuit will latch off, and it can be reset by pushing the “ON” button.

This application also illustrates how two (or more) MOSFETs can be paralleled. This reduces the switch drop, and distributes the switch dissipation into multiple packages.

High-Voltage Bootstrap (Figure 10). Although the MIC5013 is limited to operation on 7 to 32V supplies, a floating bootstrap arrangement can be used to build a high-side switch that operates on much higher voltages. The MIC5013 and MOSFET are configured as a low-side driver, but the load is connected in series with ground. The high speed normally associated with low-side drivers is retained in this circuit.

Power for the MIC5013 is supplied by a charge pump. A 20kHz square wave (15Vp-p) drives the pump capacitor and delivers current to a 100μF storage capacitor. A zener diode limits the supply to 18V. When the MIC5013 is off, power is supplied by a diode connected to a 15V supply. The circuit of Figure 8 is put to good use as a barrier between low voltage control circuitry and the 90V motor supply.

Half-Bridge Motor Driver (Figure 11). Closed loop control of motor speed requires a half-bridge driver. This topology presents an extra challenge since the two output devices should not cross conduct (shoot-through) when switching. Cross conduction increases output device power dissipation and, in the case of the MIC5013, could trip the over-current comparator. Speed is also important, since PWM control requires the outputs to switch in the 2 to 20kHz range.

The circuit of Figure 11 utilizes fast configurations for both the top- and bottom-side drivers. Delay networks at each input provide a 2 to 3μs dead time effectively eliminating cross conduction. Both the top- and bottom-side drivers are protected, so the output can be shorted to either rail without damage.

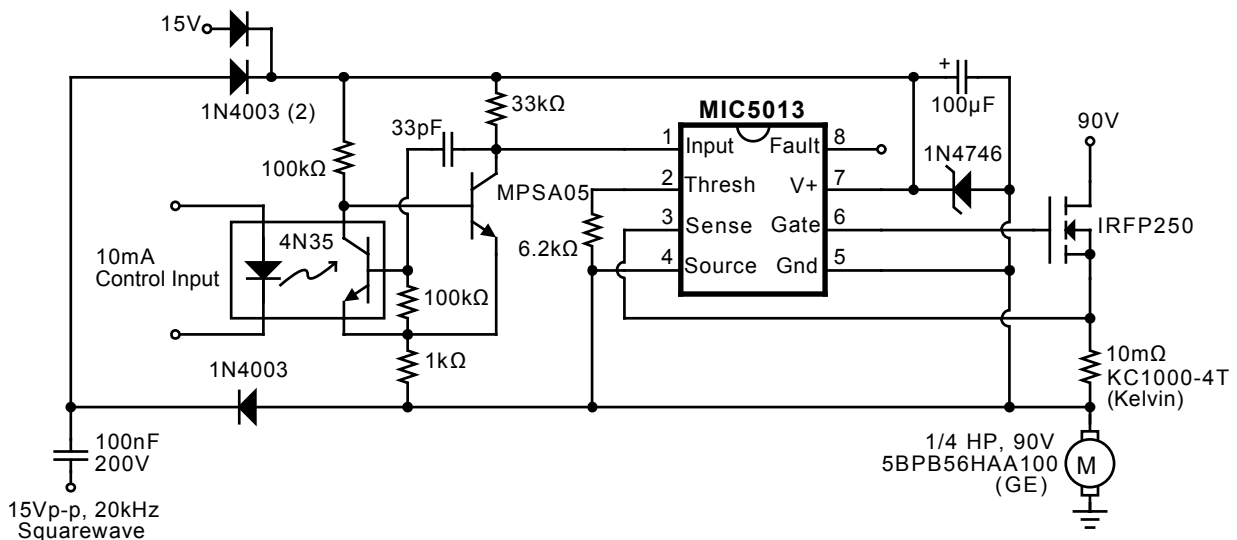


Figure 10. High-Voltage Bootstrapped Driver

Applications Information (Continued)

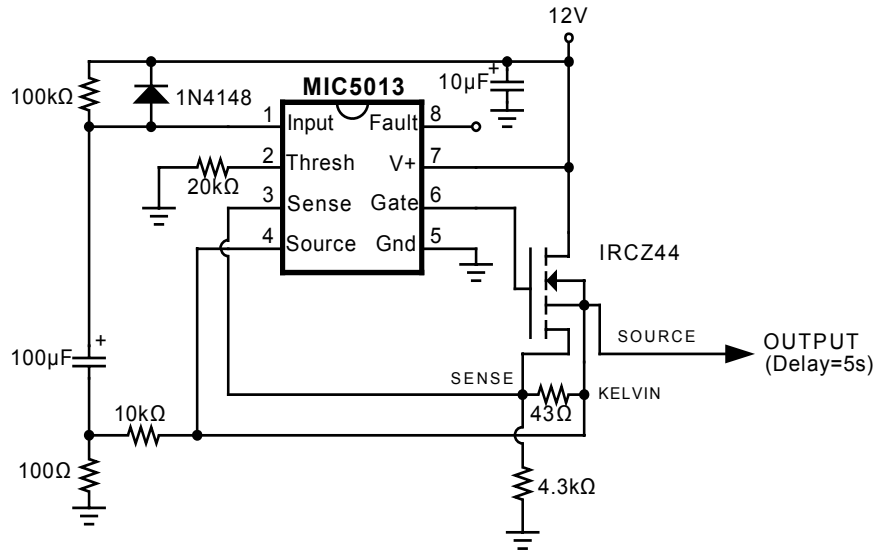


Figure 12. Time-Delay Relay with 30A Over-Current Protection

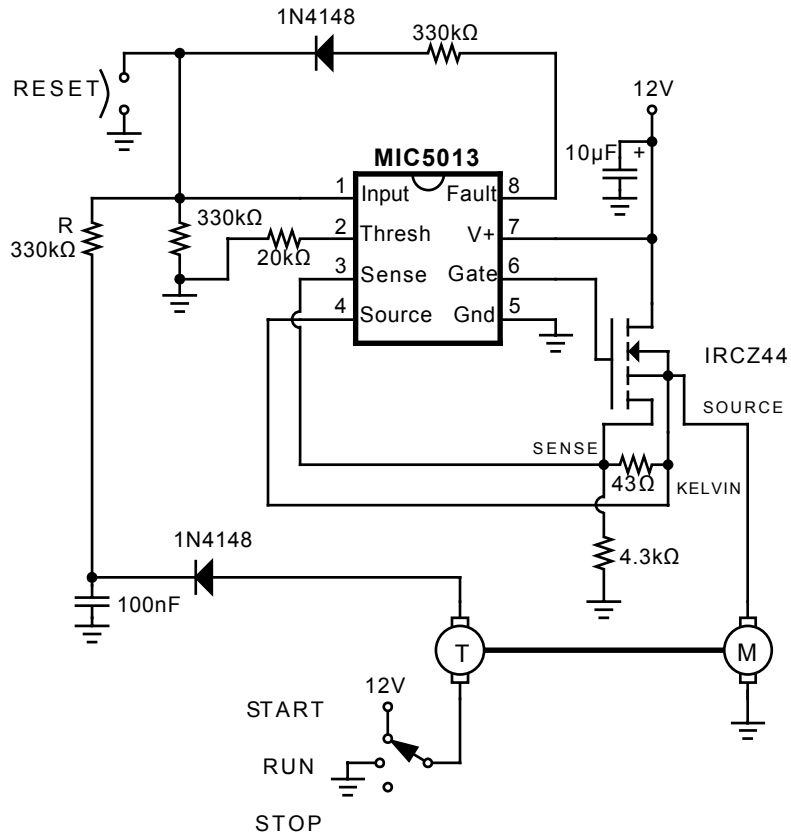


Figure 13. Motor Stall Shutdown

Applications Information (Continued)

Gate Control Circuit

When applying the MIC5010, it is helpful to understand the operation of the gate control circuitry (see Figure 14). The gate circuitry can be divided into two sections: 1) charge pump (oscillator, Q1-Q5, and the capacitors) and 2) gate turn-off switch (Q6).

When the MIC5010 is in the OFF state, the oscillator is turned off, thereby disabling the charge pump. Q5 is also turned off, and Q6 is turned on. Q6 holds the gate pin (G) at ground potential which effectively turns the external MOSFET off.

Q6 is turned off when the MIC5013 is commanded on. Q5 pulls the gate up to supply (through 2 diodes). Next, the charge pump begins supplying current to the gate. The gate accepts charge until the gate-source voltage reaches 12.5V and is clamped by the zener diode.

A 2-output, three-phase clock switches Q1-Q4, providing a quasi-tripling action. During the initial phase Q4 and Q2 are ON. C1 is discharged, and C2 is charged to supply through

Q5. For the second phase Q4 turns off and Q3 turns on, pushing pin C2 above supply (charge is dumped into the gate). Q3 also charges C1. On the third phase Q2 turns off and Q1 turns on, pushing the common point of the two capacitors above supply. Some of the charge in C1 makes its way to the gate. The sequence is repeated by turning Q2 and Q4 back on, and Q1 and Q3 off.

In a low-side application operating on a 12 to 15V supply, the MOSFET is fully enhanced by the action of Q5 alone. On supplies of more than approximately 14V, current flows directly from Q5 through the zener diode to ground. To prevent excessive current flow, the MIC5010 supply should be limited to 15V in low-side applications.

The action of Q5 makes the MIC5013 operate quickly in low-side applications. In high-side applications Q5 pre-charges the MOSFET gate to supply, leaving the charge pump to carry the gate up to full enhancement 10V above supply. Bootstrapped high-side drivers are as fast as low-side drivers since the chip supply is boosted well above the drain at turn-on.

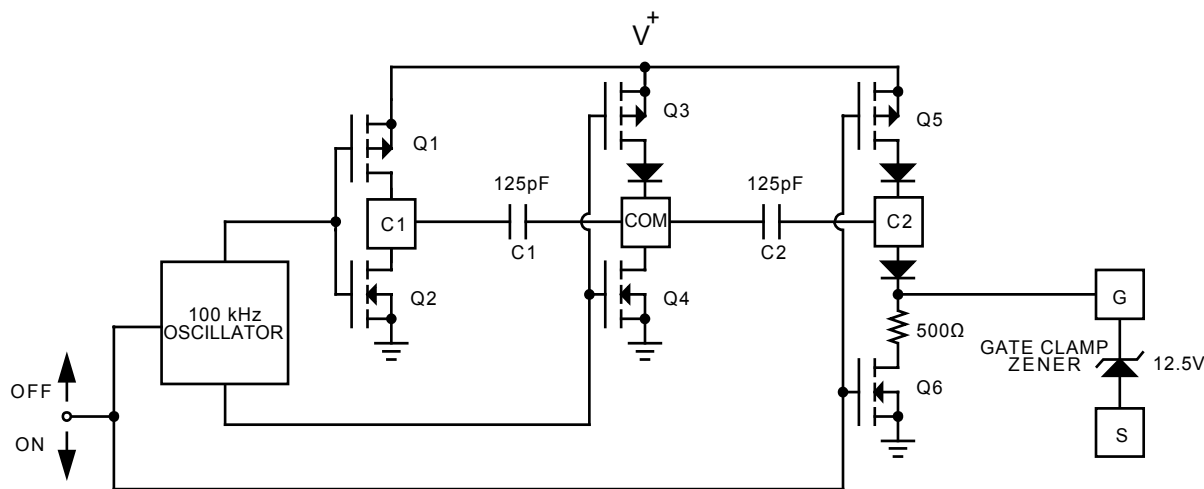
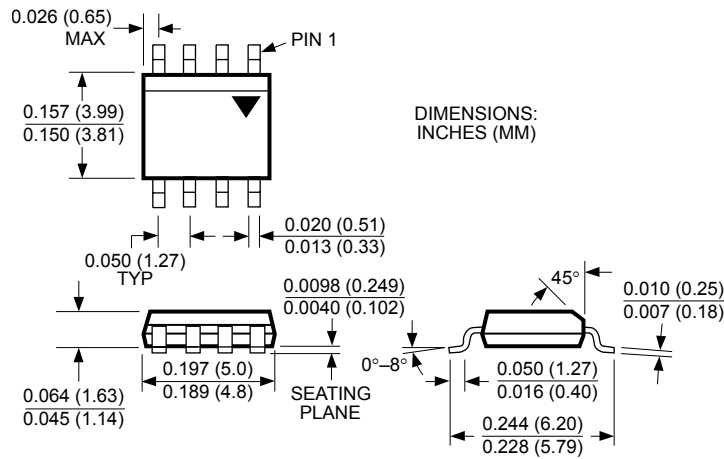
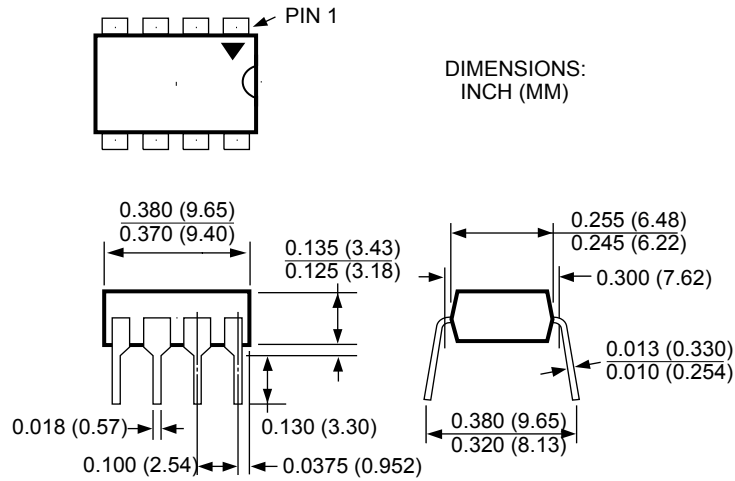


Figure 14. Gate Control Circuit Detail

Package Information



MICREL INC. 2180 FORTUNE DRIVE SAN JOSE, CA 95131 USA
 TEL + 1 (408) 944-0800 FAX + 1 (408) 474-1000 WEB <http://www.micrel.com>

This information furnished by Micrel in this data sheet is believed to be accurate and reliable. However no responsibility is assumed by Micrel for its use. Micrel reserves the right to change circuitry and specifications at any time without notification to the customer.

Micrel Products are not designed or authorized for use as components in life support appliances, devices or systems where malfunction of a product can reasonably be expected to result in personal injury. Life support devices or systems are devices or systems that (a) are intended for surgical implant into the body or (b) support or sustain life, and whose failure to perform can be reasonably expected to result in a significant injury to the user. A Purchaser's use or sale of Micrel Products for use in life support appliances, devices or systems is a Purchaser's own risk and Purchaser agrees to fully indemnify Micrel for any damages resulting from such use or sale.

Looking for pricing, stock, or lifecycle information?

Click below to explore more details on WIN SOURCE:

- ⊖ [View MIC5013YM on WIN SOURCE](#)
- ⊖ [Microchip Technology](#) Information

Optimize Your Supply Chain with WIN SOURCE Solutions

- ✓ Global Sourcing Solution
- ✓ Obsolete Management
- ✓ Cost Control Management
- ✓ Shortage Management
- ✓ Alternative Solution
- ✓ Excess Inventory Management